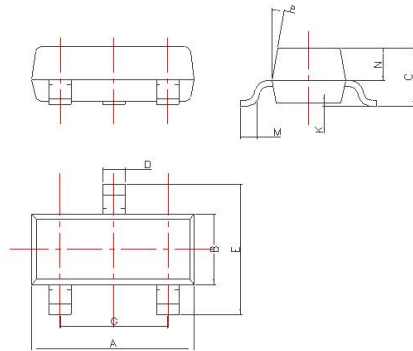
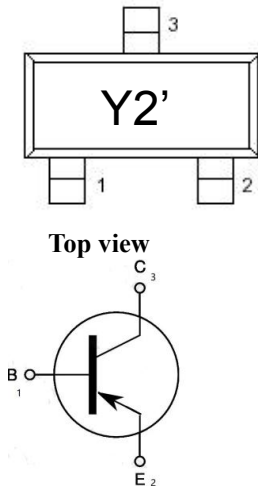


CDT8550-ME(Sn)

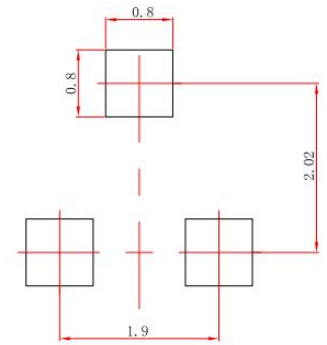
TRANSISTOR

Marking: Y2'

SOT-23 Dimension

SOT-23
Suggested Layout

| DIM | Millimeters |
|-----|-------------|
| A | 2.85~3.04 |
| B | 1.30±0.10 |
| C | 1.00±0.10 |
| D | 0.45±0.05 |
| E | 2.25~2.55 |
| G | 1.90±0.1 |
| K | 0.00-0.10 |
| M | 0.20 min |
| N | 0.60±0.10 |
| P | 7±2° |



mm(±0.05mm)

MAXIMUM RATINGS (Ta=25°C)

| Characteristic | Symbol | Rating | Unit |
|--------------------------------|------------------|--------|------|
| Collector-Emitter Voltage | V _{CEO} | -25 | Vdc |
| Collector-Base Voltage | V _{CB0} | -40 | Vdc |
| Emitter-Base Voltage | V _{EBO} | -5.0 | Vdc |
| Collector Current - Continuous | I _C | -1500 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|----------------------------------|--------------------------------------|-------------------|------|
| Collector Power Dissipation | P _c | 300 | mW |
| Junction and Storage Temperature | T _j , T _{stg} | 150 , -55 ~150 | °C |

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise noted)

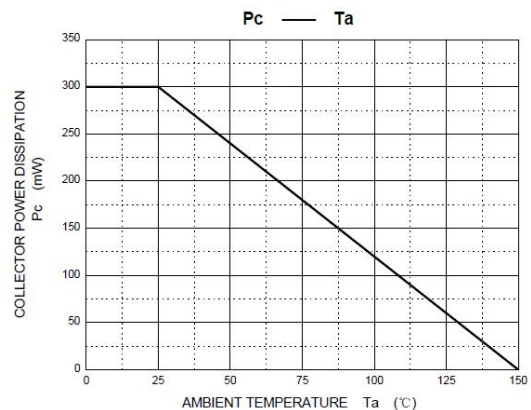
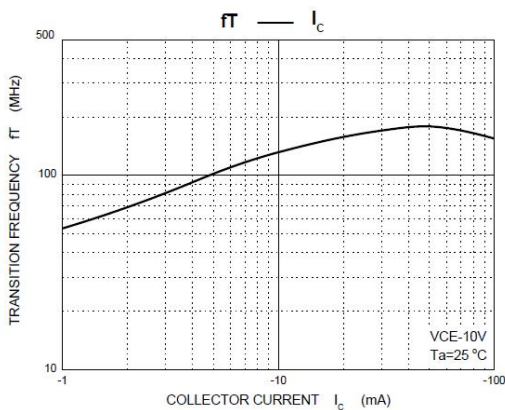
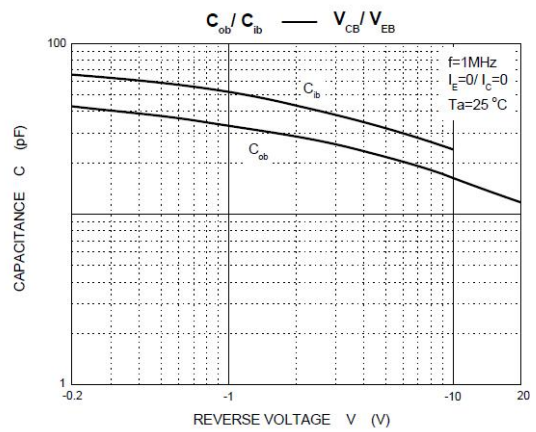
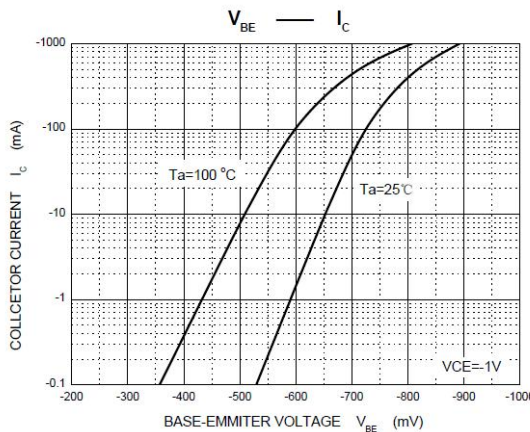
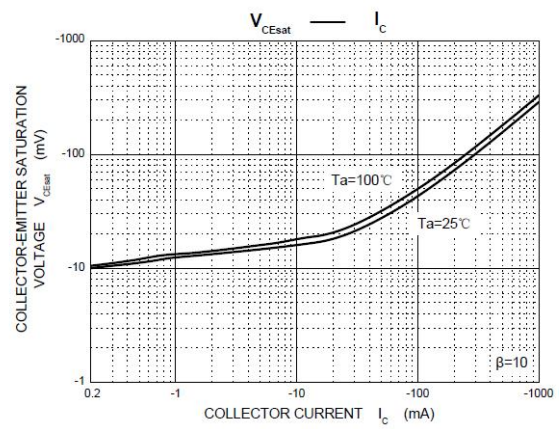
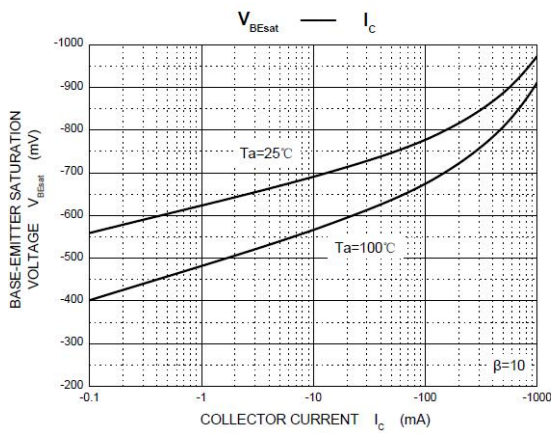
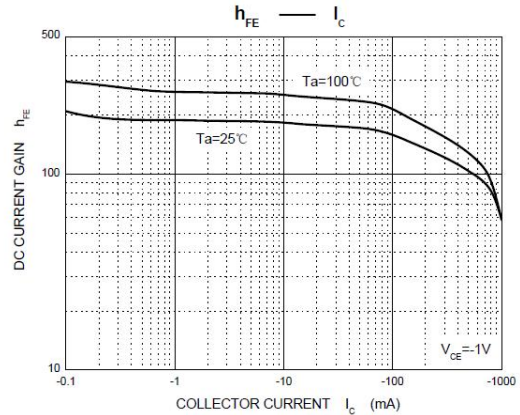
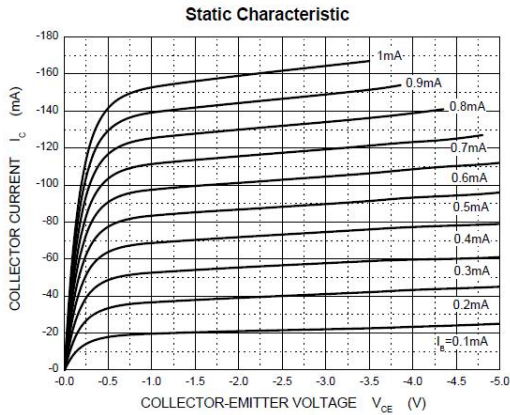
| Characteristic | Symbol | Test Condition | Min | Type | Max | Unit |
|--------------------------------------|----------------------|---|------|------|------|------|
| Collector Cutoff Current | I _{CB0} | V _{CB} =-30V, I _E =0 | -- | -- | -0.1 | μA |
| Collector- Emitter Cutoff Current | I _{CEO} | V _{CB} =-20V, I _E =0 | -- | -- | -0.1 | μA |
| Emitter Cutoff Current | I _{EBO} | V _{EB} =-5V, I _C =0 | -- | -- | -0.1 | μA |
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | I _C =-10mA | -25 | -- | -- | V |
| Collector- Base Breakdown Voltage | V _{(BR)CBO} | I _C =-100μA | -40 | -- | -- | V |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | I _E =-100μA | -5 | -- | -- | V |
| DC Current Gain | h _{FE(1)} | V _{CE} =-1V, I _C =-100mA | 200 | -- | 350 | -- |
| | h _{FE(2)} | V _{CE} =-1V, I _C =-1.2A | 40 | -- | -- | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | I _C =-1.2A, I _B =-120mA | -- | -- | -0.6 | V |
| Base Emitter Voltage | V _{BE} | V _{CE} =-1V, I _C =-10mA | -100 | -0.8 | -1.2 | V |
| Transition Frequency | f _T | V _{CE} =-5V, I _C =-10mA | -- | 120 | -- | MHz |
| Collector Output Capacitance | V _{ob} | V _{CB} =-10V, I _E =0, f=1MHz | -- | 13 | 30 | pF |

- FR-5=1.0x0.75x0.062in.
- Alumina=0.4x0.3x0.024in, 99.5% alumina.
- Pulse Width ≤300μS; Duty Cycle ≤2.0%.

CDT8550-ME(Sn)

TRANSISTOR

Typical Characteristics



Note: Specifications are subject to change without notice. For more detail and update, please visit our website.